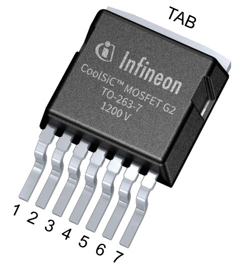
Final datasheet

CoolSiC™ 1200 V SiC MOSFET G2 : Silicon Carbide MOSFET



Halogen-free
Green
Lead-free
RoHS

Features

- V_{DSS} = 1200 V at T_{vj} = 25°C
- I_{DDC} = 53 A at T_C = 100°C
- $R_{DS(on)}$ = 25.4 mΩ at V_{GS} = 18 V, T_{vj} = 25°C
- Very low switching losses
- Overload operation up to T_{vj} = 200°C
- Short circuit withstand time 2 µs
- Benchmark gate threshold voltage, $V_{GS(th)}$ = 4.2 V
- Robust against parasitic turn on, 0 V turn-off gate voltage can be applied
- Robust body diode for hard commutation
- .XT interconnection technology for best-in-class thermal performance
- Suitable Infineon gate drivers can be found under https://www.infineon.com/gdfinder

Potential applications

- EV Charging
- Online UPS / Industrial UPS
- String inverter
- General purpose drives (GPD)

Product validation

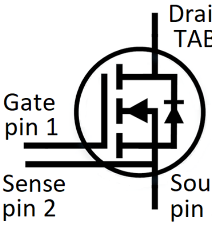
- Qualified for industrial applications according to the relevant tests of JEDEC47/20/22

Description

Pin definition:

• Pin 1 - Gate
• Pin 2 - Kelvin sense contact
• Pin 3…7 - Source
• Tab - Drain

Note: the source and sense pins are not exchangeable, their exchange might lead to malfunction (only for 4pin, TO263-7L)



Type	Package	Marking
IMBG120R026M2H	PG-TO263-7-U01	12M2H026

Table of contents

1 Package

Table 1 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Storage temperature	T_{stg}		-55		150	°C
Soldering temperature	T_{sold}	Reflow soldering (MSL1 according to JEDEC J-STD-020)			260	°C
Thermal resistance, junction-ambient	$R_{th(j-a)}$				62	K/W
MOSFET/body diode thermal resistance, junction-case	$R_{th(j-c)}$			0.34	0.44	K/W

2 MOSFET

Table 2 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Drain-source voltage	V_{DSS}	$T_{vj} \geq 25$ °C		1200	V
Continuous DC drain current for $R_{th(j-c,max)}$, limited by $T_{vj(max)}$	I_{DDC}	$V_{GS} = 18$ V	$T_c = 25$ °C	75	A
			$T_c = 100$ °C	53	
Peak drain current, t_p limited by $T_{vj(max)}$ 1)	I_{DM}	$V_{GS} = 18$ V		265	A
Gate-source voltage, max. transient voltage	V_{GS}	$t_p \leq 0.5$ µs, $D < 0.01$		-10...25	V
Gate-source voltage, max. static voltage 2)	V_{GS}			-7...23	V
Avalanche energy, single pulse	E_{AS}	$I_D = 27.3$ A, $V_{DD} = 50$ V, $L = 0.9$ mH, $T_{vj(start)} = 25$ °C		343	mJ
Avalanche energy, repetitive	E_{AR}	$I_D = 27.3$ A, $V_{DD} = 50$ V, $L = 4.6$ µH, $T_{vj(start)} = 25$ °C		1.69	mJ
Short-circuit withstand time	t_{SC}	$V_{DD} \leq 800$ V, $V_{DS,peak} < 1200$ V, $V_{GS(on)} = 15$ V, $T_{vj(start)} = 25$ °C		2	µs
Power dissipation, limited by $T_{vj(max)}$	P_{tot}		$T_c = 25$ °C	335	W
			$T_c = 100$ °C	168	

1) verified by design.
2) The maximum gate-source voltage in the application design should be in accordance to IPC-9592B.

Table 3 Recommended values

Parameter	Symbol	Note or test condition	Values	Unit
Recommended turn-on gate voltage	$V_{GS(on)}$		15...18	V
Recommended turn-off gate voltage	$V_{GS(off)}$		-5...0	V

Table 4 Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Drain-source on-state resistance	$R_{DS(on)}$	I_D = 27.3 A	T_{vj} = 25 °C, $V_{GS(on)}$ = 18 V		25.4		mΩ
			T_{vj} = 150 °C, $V_{GS(on)}$ = 18 V		52	68	
			T_{vj} = 175 °C, $V_{GS(on)}$ = 18 V		60		
			T_{vj} = 25 °C, $V_{GS(on)}$ = 15 V		31.7		
Gate-source threshold voltage	$V_{GS(th)}$	I_D = 8.6 mA, V_{DS} = V_{GS} (tested after 1 ms pulse at V_{GS} = 20 V)	T_{vj} = 25 °C	3.5	4.2	5.1	V
			T_{vj} = 175 °C		3.2		
Zero gate-voltage drain current	I_{DSS}	V_{DS} = 1200 V, V_{GS} = 0 V	T_{vj} = 25 °C			240	µA
			T_{vj} = 175 °C		4		
Gate leakage current	I_{GSS}	V_{DS} = 0 V	V_{GS} = 23 V			120	nA
			V_{GS} = -10 V			-120	
Forward transconductance	g_{fs}	I_D = 27.3 A, V_{DS} = 20 V			18.3		S
Internal gate resistance	$R_{G,int}$	f = 1 MHz, V_{AC} = 25 mV			5.6		Ω
Input capacitance	C_{iss}	V_{DS} = 800 V, V_{GS} = 0 V, f = 100 kHz, V_{AC} = 25 mV			1990		pF
Output capacitance	C_{oss}	V_{DS} = 800 V, V_{GS} = 0 V, f = 100 kHz, V_{AC} = 25 mV			85		pF
Reverse transfer capacitance	C_{rss}	V_{DS} = 800 V, V_{GS} = 0 V, f = 100 kHz, V_{AC} = 25 mV			7.4		pF
C_{oss} stored energy	E_{oss}	Calculated based on C_{oss} = f(V_{DD})			36		µJ
Output charge	Q_{oss}	Calculated based on C_{oss} = f(V_{DD})			132.6		nC
Effective output capacitance, energy related	$C_{o(er)}$	V_{DS} = 0...800 V, V_{GS} = 0 V, Calculated based on E_{oss}			112.5		pF
Effective output capacitance, time related	$C_{o(tr)}$	I_D = constant, V_{DS} = 0...800 V, V_{GS} = 0 V, Calculated based on Q_{oss}			165.7		pF
Total gate charge	Q_G	V_{DD} = 800 V, I_D = 27.3 A, V_{GS} = 0/18 V, turn-on pulse			60		nC

(table continues...)

Table 4 (continued) Characteristic values

Parameter	Symbol	Note or test condition		Min.	Typ.	Max.	Unit
Plateau gate charge	$Q_{GS(pl)}$	V_{DD} = 800 V, I_D = 27.3 A, V_{GS} = 0/18 V, turn-on pulse			12.9		nC
Gate-drain charge	Q_{GD}	V_{DD} = 800 V, I_D = 27.3 A, V_{GS} = 0/18 V, turn-on pulse			16.2		nC
Turn-on delay time	$t_{d(on)}$	V_{DD} = 800 V, I_D = 27.3 A, V_{GS} = 0/18 V, $R_{G,ext}$ = 2.3 Ω, $L_σ$ = 15 nH, diode: body diode at V_{GS} = 0 V	T_{vj} = 25 °C		5		ns
			T_{vj} = 175 °C		4.9		
Rise time	t_r	V_{DD} = 800 V, I_D = 27.3 A, V_{GS} = 0/18 V, $R_{G,ext}$ = 2.3 Ω, $L_σ$ = 15 nH, diode: body diode at V_{GS} = 0 V	T_{vj} = 25 °C		16.2		ns
			T_{vj} = 175 °C		15.9		
Turn-off delay time	$t_{d(off)}$	V_{DD} = 800 V, I_D = 27.3 A, V_{GS} = 0/18 V, $R_{G,ext}$ = 2.3 Ω, $L_σ$ = 15 nH, diode: body diode at V_{GS} = 0 V	T_{vj} = 25 °C		9.7		ns
			T_{vj} = 175 °C		16.9		
Fall time	t_f	V_{DD} = 800 V, I_D = 27.3 A, V_{GS} = 0/18 V, $R_{G,ext}$ = 2.3 Ω, $L_σ$ = 15 nH, diode: body diode at V_{GS} = 0 V	T_{vj} = 25 °C		6.3		ns
			T_{vj} = 175 °C		7.4		
Turn-on energy	E_{on}	V_{DD} = 800 V, I_D = 27.3 A, V_{GS} = 0/18 V, $R_{G,ext}$ = 2.3 Ω, $L_σ$ = 15 nH, diode: body diode at V_{GS} = 0 V	T_{vj} = 25 °C		211		μJ
			T_{vj} = 175 °C		406		
Turn-off energy	E_{off}	V_{DD} = 800 V, I_D = 27.3 A, V_{GS} = 0/18 V, $R_{G,ext}$ = 2.3 Ω, $L_σ$ = 15 nH, diode: body diode at V_{GS} = 0 V	T_{vj} = 25 °C		44		μJ
			T_{vj} = 175 °C		67		
Total switching energy[1)]	E_{tot}	V_{DD} = 800 V, I_D = 27.3 A, V_{GS} = 0/18 V, $R_{G,ext}$ = 2.3 Ω, $L_σ$ = 15 nH, diode: body diode at V_{GS} = 0 V	T_{vj} = 25 °C		315		μJ
			T_{vj} = 175 °C		653		

(table continues...)

Table 4 (continued) Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Turn-on energy at -5 V	E_{on}	V_{DD} = 800 V, I_D = 27.3 A, V_{GS} = -5/18 V, $R_{G,ext}$ = 2.3 Ω, $L_σ$ = 15 nH, diode: body diode at V_{GS} = -5 V	T_{vj} = 25 °C		241		µJ
			T_{vj} = 175 °C		478		
Turn-off energy at -5 V	E_{off}	V_{DD} = 800 V, I_D = 27.3 A, V_{GS} = -5/18 V, $R_{G,ext}$ = 2.3 Ω, $L_σ$ = 15 nH, diode: body diode at V_{GS} = -5 V	T_{vj} = 25 °C		47		µJ
			T_{vj} = 175 °C		52		
Total switching energy at -5 V[1)]	E_{tot}	V_{DD} = 800 V, I_D = 27.3 A, V_{GS} = -5/18 V, $R_{G,ext}$ = 2.3 Ω, $L_σ$ = 15 nH, diode: body diode at V_{GS} = -5 V	T_{vj} = 25 °C		355		µJ
			T_{vj} = 175 °C		760		
Virtual junction temperature	T_{vj}			-55		175	°C
Virtual junction temperature	$T_{vj(over)}$	overload, cumulative max. 100 h[2)]				200	°C

1) including E_{fr}
2) up to 5000 cycles. Maximum ΔT limited to 100 K.

***Note**: The chip technology was characterized up to 200 kV/µs. The measured dV/dt was limited by measurement test setup and package.*

Characteristics at T_{vj} = 25°C, unless otherwise specified.

3 Body diode (MOSFET)

Table 5 Maximum rated values

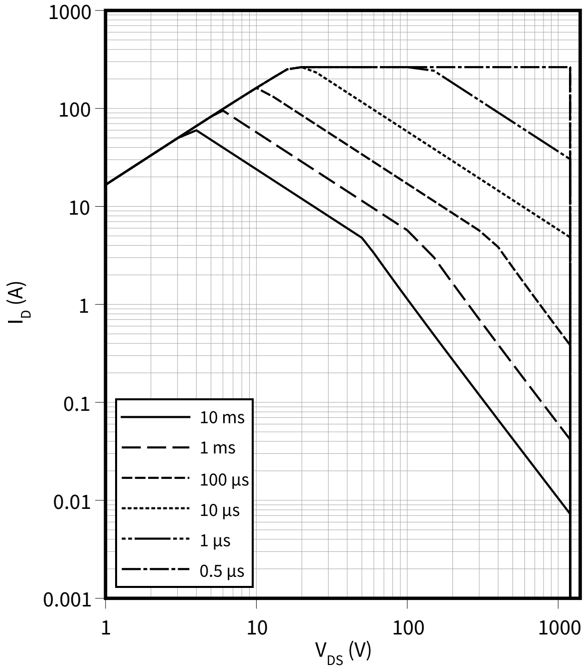
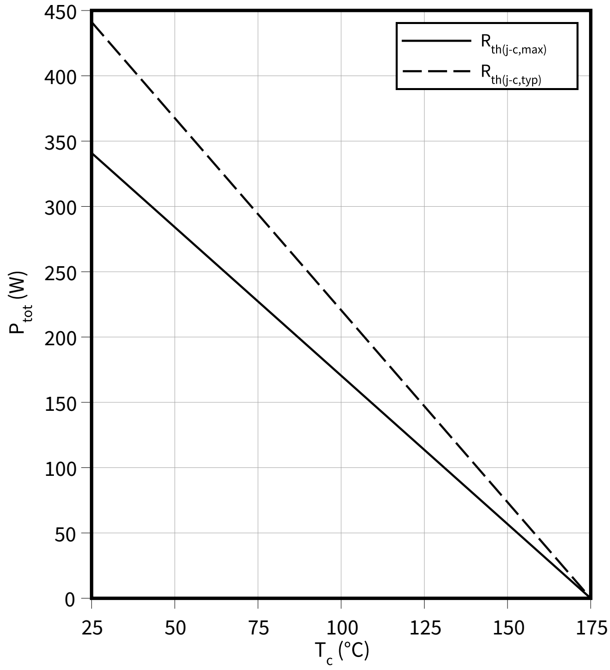
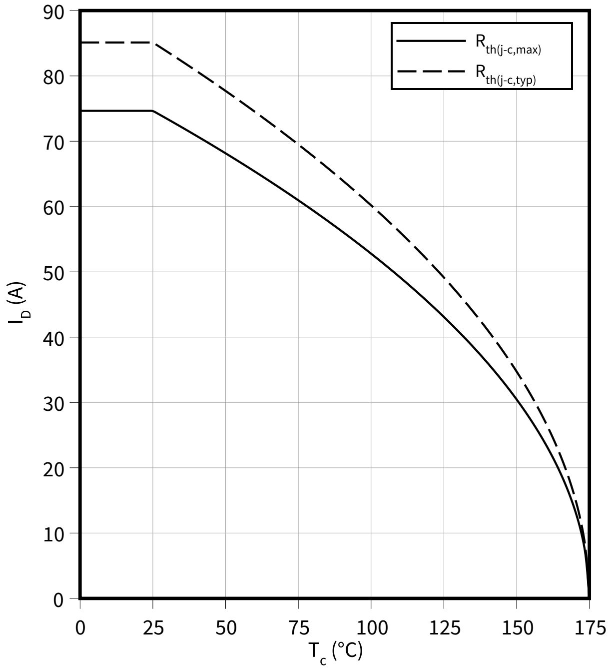
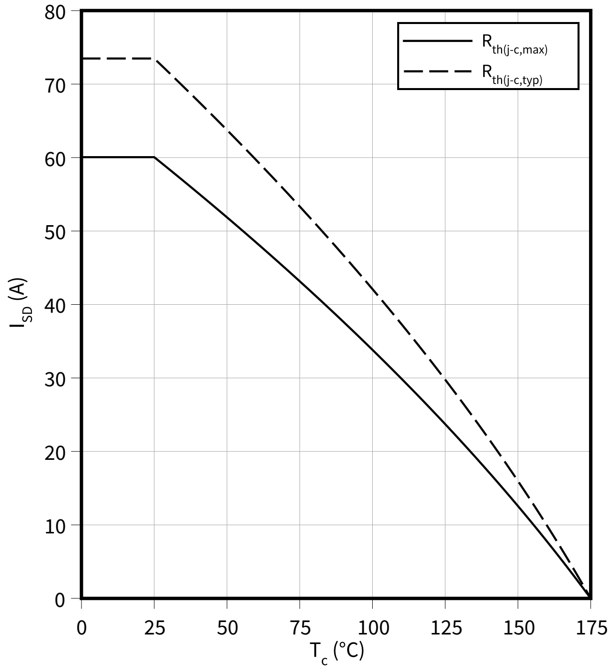
Parameter	Symbol	Note or test condition		Values	Unit
Drain-source voltage	V_{DSS}	T_{vj} ≥ 25 °C		1200	V
Continuous reverse drain current for $R_{th(j-c,max)}$, limited by $T_{vj(max)}$	I_{SDC}	V_{GS} = 0 V	T_c = 25 °C	61	A
			T_c = 100 °C	34.8	
Peak reverse drain current, t_p limited by $T_{vj(max)}$	I_{SM}	V_{GS} = 0 V		162	A

Table 6 **Characteristic values**

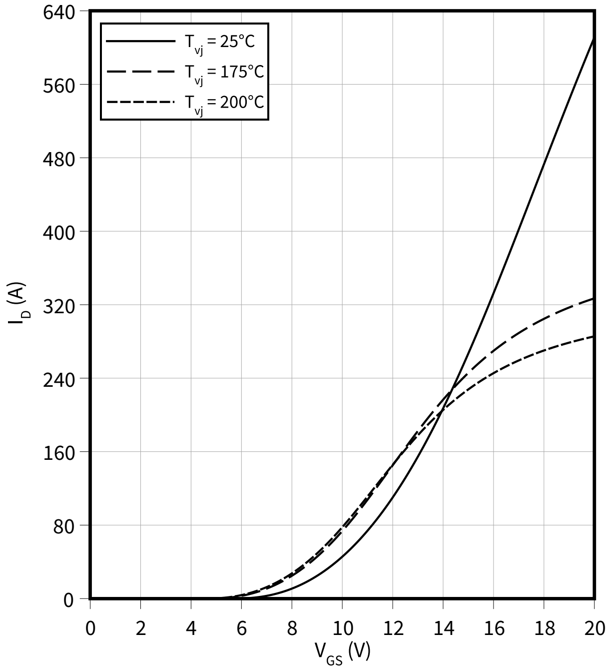
Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Drain-source reverse voltage	V_{SD}	I_{SD} = 27.3 A, V_{GS} = 0 V	T_{vj} = 25 °C		4.2	5.5	V
			T_{vj} = 100 °C		4.11		
			T_{vj} = 175 °C		4.05		
MOSFET forward recovery charge	Q_{fr}	V_{DD} = 800 V, I_{SD} = 27.3 A, V_{GS} = 0 V, $R_{G,ext}$ = 2.3 Ω, Q_{fr} includes also Q_C	T_{vj} = 25 °C		0.65		µC
			T_{vj} = 175 °C		0.9		
MOSFET peak forward recovery current	I_{frm}	V_{DD} = 800 V, I_{SD} = 27.3 A, V_{GS} = 0 V, $R_{G,ext}$ = 2.3 Ω, Q_{fr} includes also Q_C	T_{vj} = 25 °C		33		A
			T_{vj} = 175 °C		57		
MOSFET forward recovery energy	E_{fr}	V_{DD} = 800 V, I_{SD} = 27.3 A, V_{GS} = 0 V, $R_{G,ext}$ = 2.3 Ω, Q_{fr} includes also Q_C	T_{vj} = 25 °C		60		µJ
			T_{vj} = 175 °C		180		
MOSFET forward recovery energy at -5 V	E_{fr}	V_{DD} = 800 V, I_{SD} = 27.3 A, V_{GS} = -5 V, $R_{G,ext}$ = 2.3 Ω, Q_{fr} includes also Q_C	T_{vj} = 25 °C		67		µJ
			T_{vj} = 175 °C		230		
Virtual junction temperature	T_{vj}			-55		175	°C
Virtual junction temperature	$T_{vj(over)}$	overload, cumulative max. 100 h[1)]				200	°C

1) up to 5000 cycles. Maximum ΔT limited to 100 K.

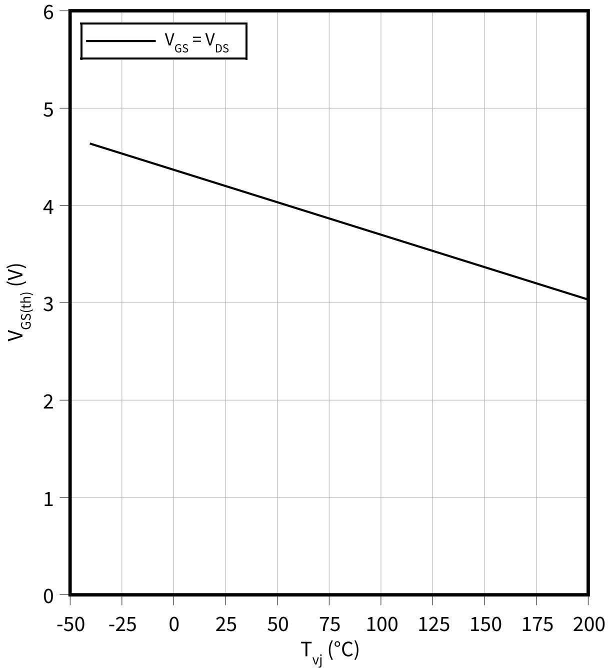
4 Characteristics diagrams

Safe operating area (SOA) $I_D = f(V_{DS})$ $T_{vj} \le 175$ °C, $T_c = 25$ °C	Power dissipation as a function of case temperature $P_{tot} = f(T_c)$
	
Maximum DC drain to source current as a function of case temperature limited by bond wire $I_D = f(T_c)$	**Maximum source to drain current as a function of case temperature limited by bond wire** $I_{SD} = f(T_c)$ $V_{GS} = 0$ V
	

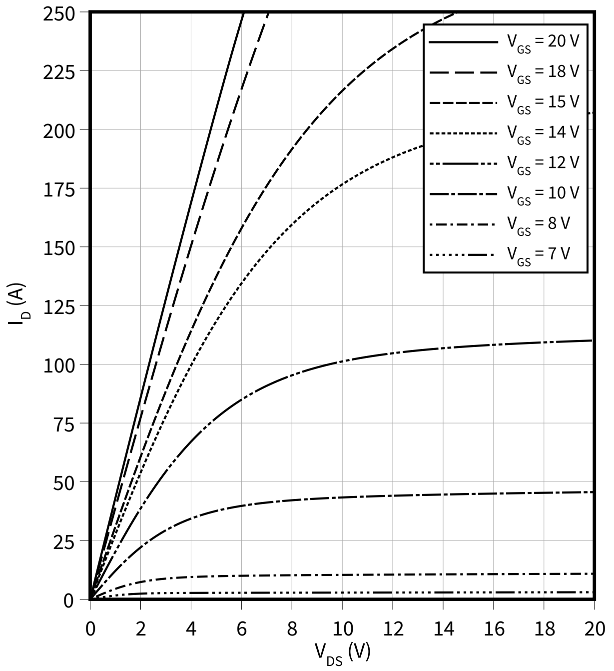
Typical transfer characteristic
$I_D = f(V_{GS})$
$V_{DS} = 20$ V, $t_p = 20$ µs



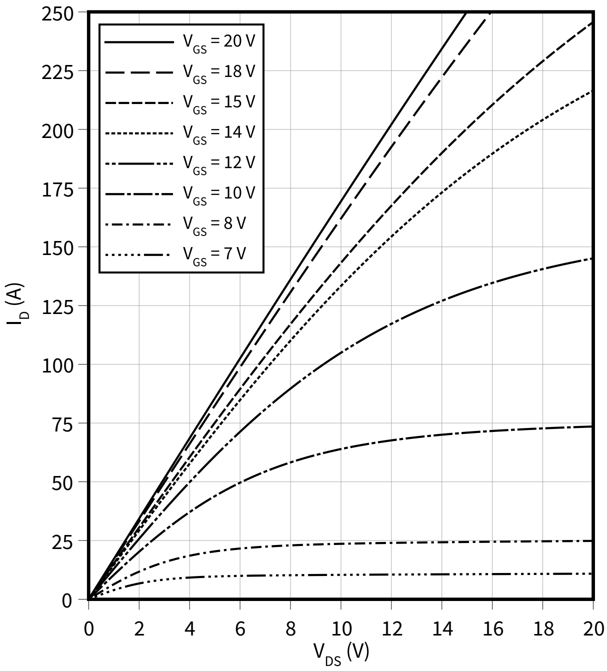
Typical gate-source threshold voltage as a function of junction temperature
$V_{GS(th)} = f(T_{vj})$
$I_D = 8.6$ mA



Typical output characteristic, V_{GS} as a parameter
$I_D = f(V_{DS})$
$T_{vj} = 25$ °C, $t_p = 20$ µs



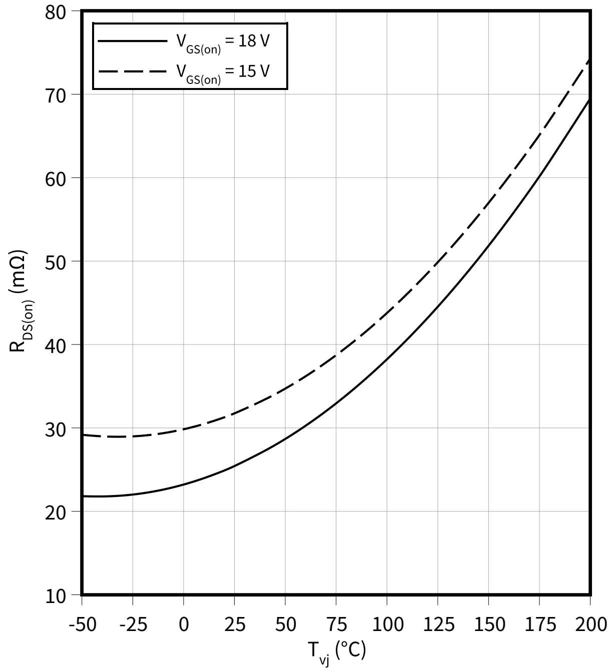
Typical output characteristic, V_{GS} as a parameter
$I_D = f(V_{DS})$
$T_{vj} = 175$ °C, $t_p = 20$ µs



Typical on-state resistance as a function of junction temperature

$R_{DS(on)} = f(T_{vj})$

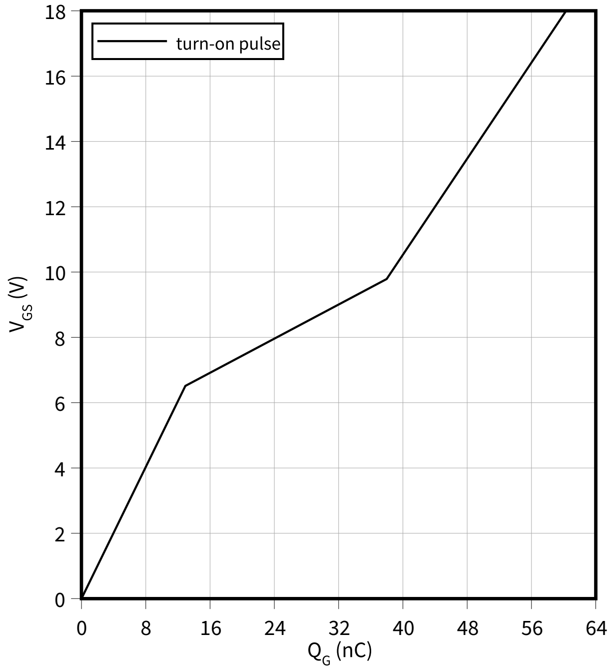
$I_D = 27.3$ A



Typical gate charge

$V_{GS} = f(Q_G)$

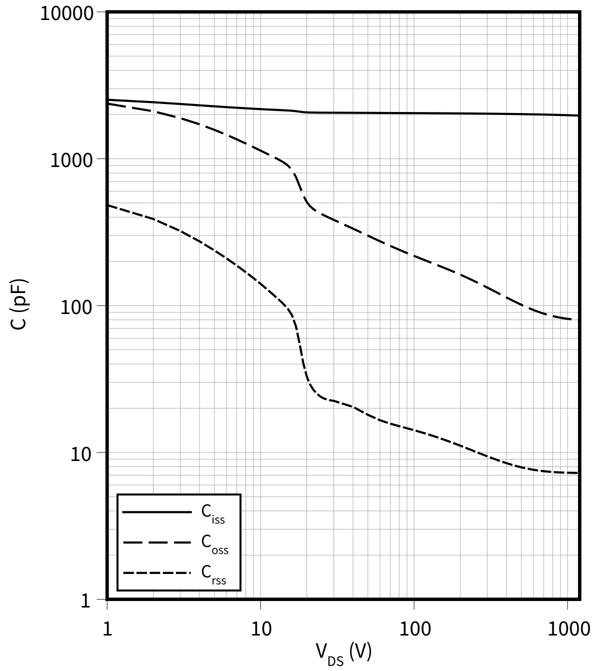
$I_D = 27.3$ A, $V_{DS} = 800$ V



Typical capacitance as a function of drain-source voltage

$C = f(V_{DS})$

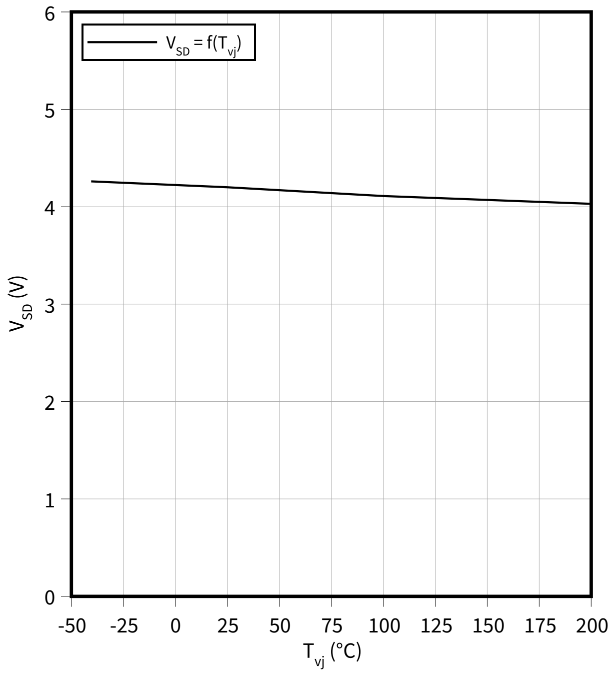
f = 100 kHz, $V_{GS} = 0$ V



Typical reverse drain voltage as a function of junction temperature

$V_{SD} = f(T_{vj})$

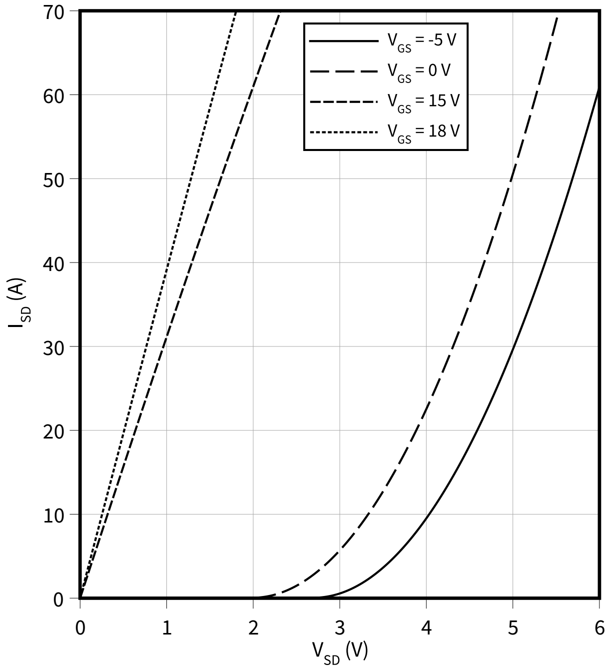
$I_{SD} = 27.3$ A, $V_{GS} = 0$ V



Typical reverse drain current as a function of reverse drain voltage, V_{GS} as a parameter

$I_{SD} = f(V_{SD})$

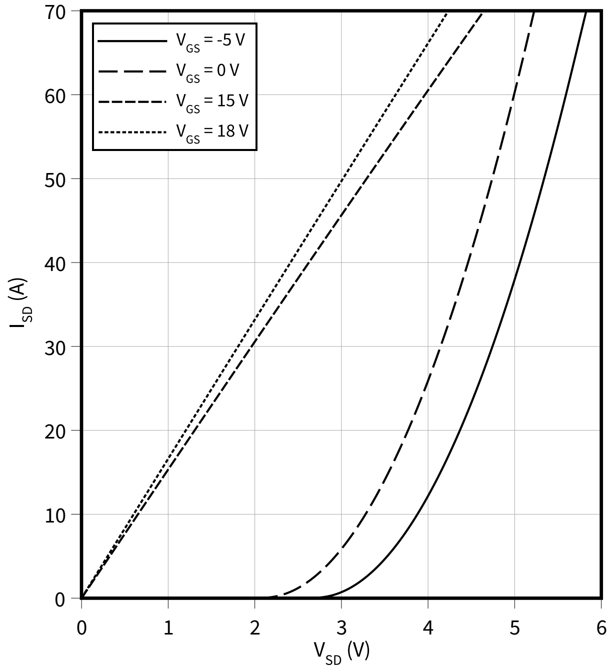
$T_{vj} = 25\ °C$, $t_p = 20\ \mu s$



Typical reverse drain current as a function of reverse drain voltage, V_{GS} as a parameter

$I_{SD} = f(V_{SD})$

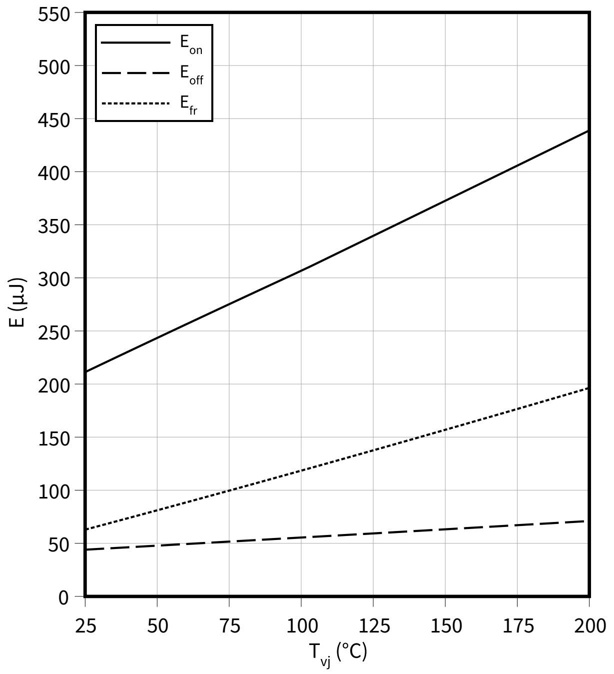
$T_{vj} = 175\ °C$, $t_p = 20\ \mu s$



Typical switching energy as a function of junction temperature, test circuit in Fig. F, 2nd device own body diode: V_{GS} = 0 V

$E = f(T_{vj})$

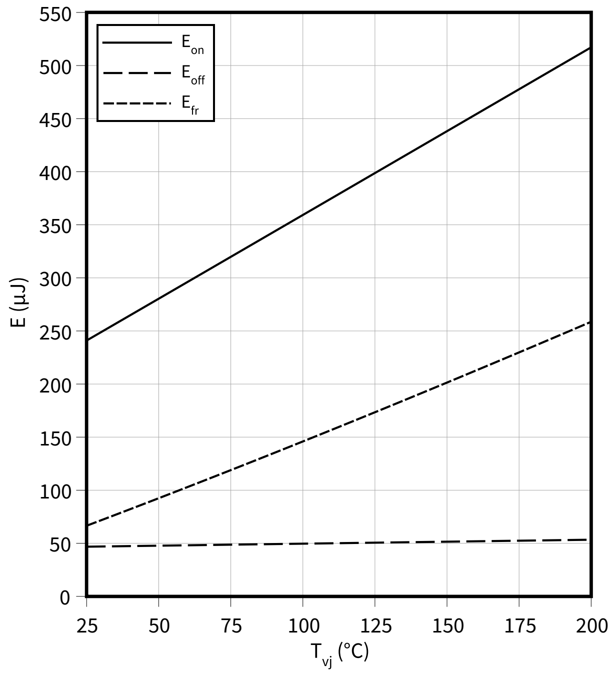
$V_{GS} = 0/18\ V$, $I_D = 27.3\ A$, $R_{G,ext} = 2.3\ \Omega$, $V_{DD} = 800\ V$



Typical switching energy as a function of junction temperature, test circuit in Fig. F, 2nd device own body diode: V_{GS} = -5 V

$E = f(T_{vj})$

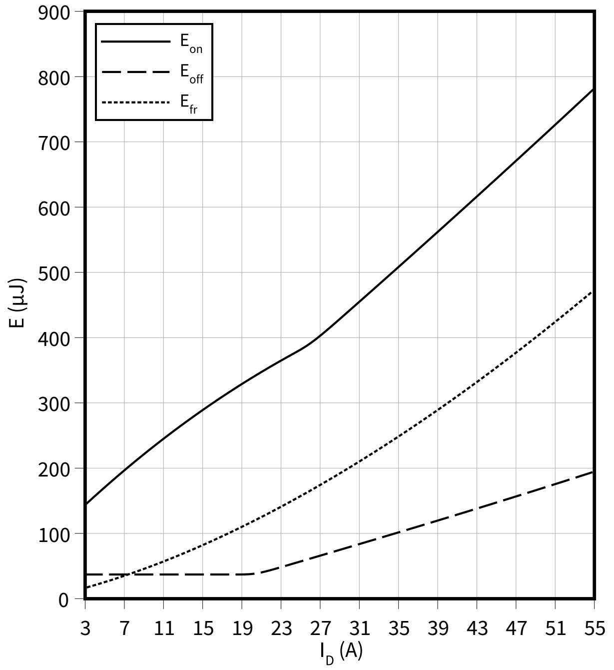
$V_{GS} = -5/18\ V$, $I_D = 27.3\ A$, $R_{G,ext} = 2.3\ \Omega$, $V_{DD} = 800\ V$



Typical switching energy as a function of drain current, test circuit in Fig. F, 2nd device own body diode: V_{GS} = 0 V

E = f(I_D)

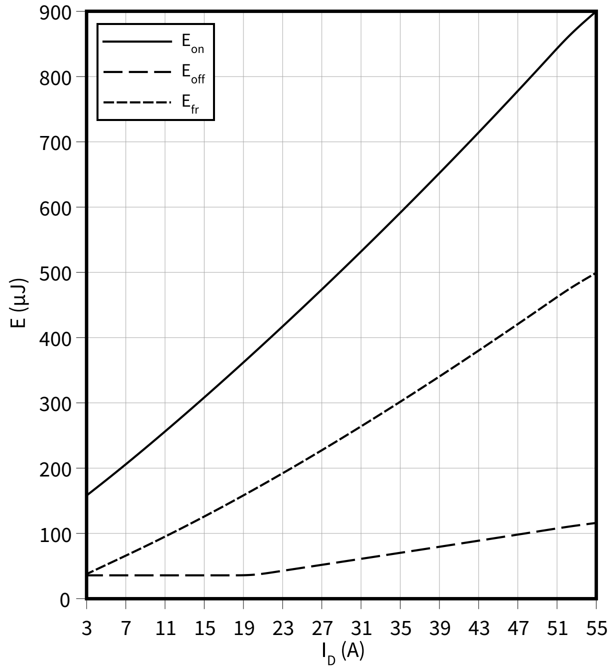
V_{GS} = 0/18 V, T_{vj} = 175 °C, $R_{G,ext}$ = 2.3 Ω, V_{DD} = 800 V



Typical switching energy as a function of drain current, test circuit in Fig. F, 2nd device own body diode: V_{GS} = -5 V

E = f(I_D)

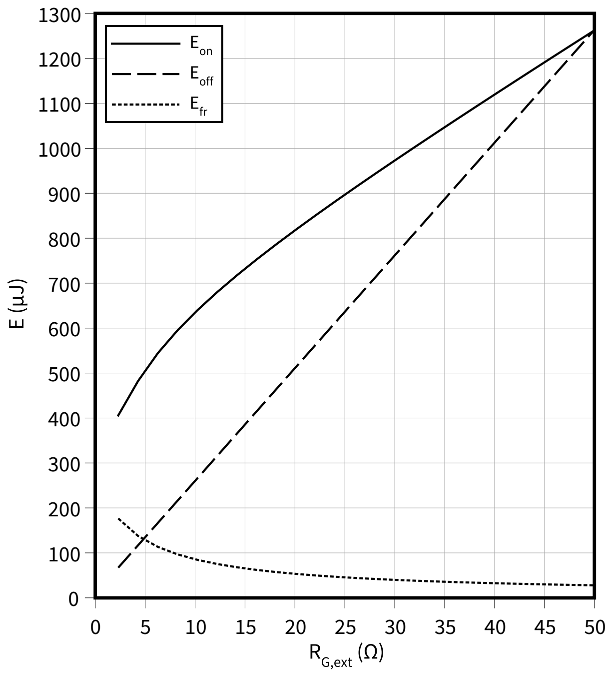
V_{GS} = -5/18 V, T_{vj} = 175 °C, $R_{G,ext}$ = 2.3 Ω, V_{DD} = 800 V



Typical switching energy as a function of gate resistance, test circuit in Fig. F, 2nd device own body diode: V_{GS} = 0 V

E = f($R_{G,ext}$)

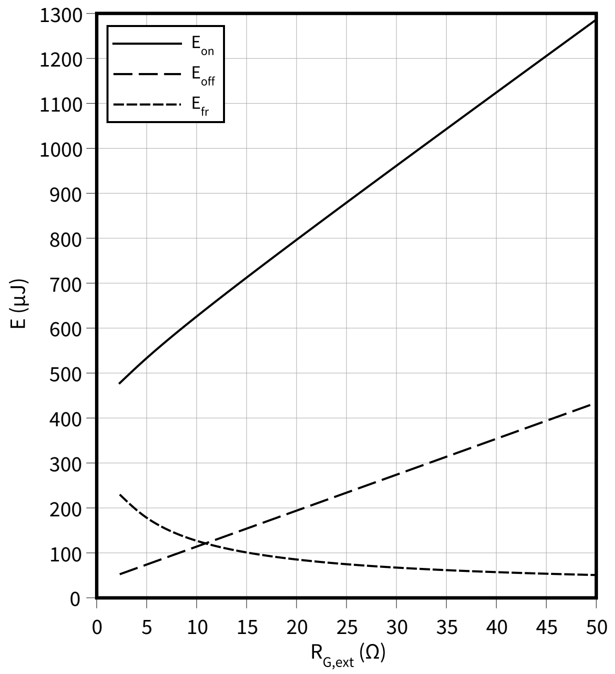
V_{GS} = 0/18 V, I_D = 27.3 A, T_{vj} = 175 °C, V_{DD} = 800 V



Typical switching energy as a function of gate resistance, test circuit in Fig. F, 2nd device own body diode: V_{GS} = -5 V

E = f($R_{G,ext}$)

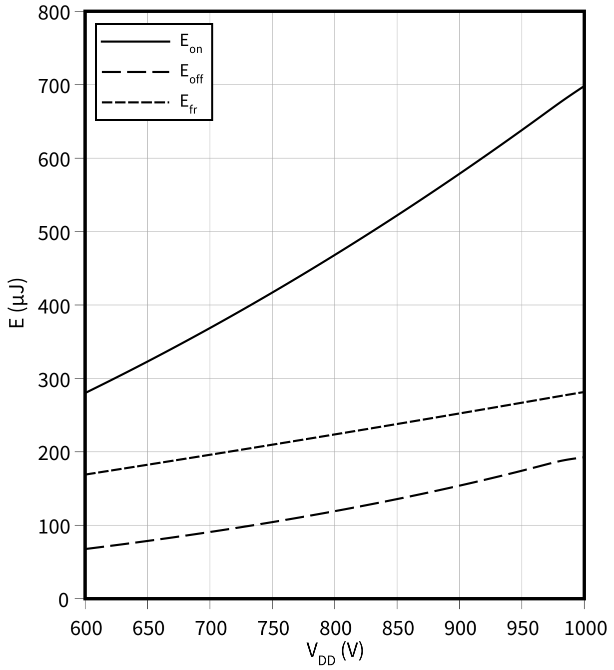
V_{GS} = -5/18 V, I_D = 27.3 A, T_{vj} = 175 °C, V_{DD} = 800 V



Typical switching energy as a function of DC link voltage, test circuit in Fig. F, 2nd device own body diode: V_{GS} = 0 V

$E = f(V_{DD})$

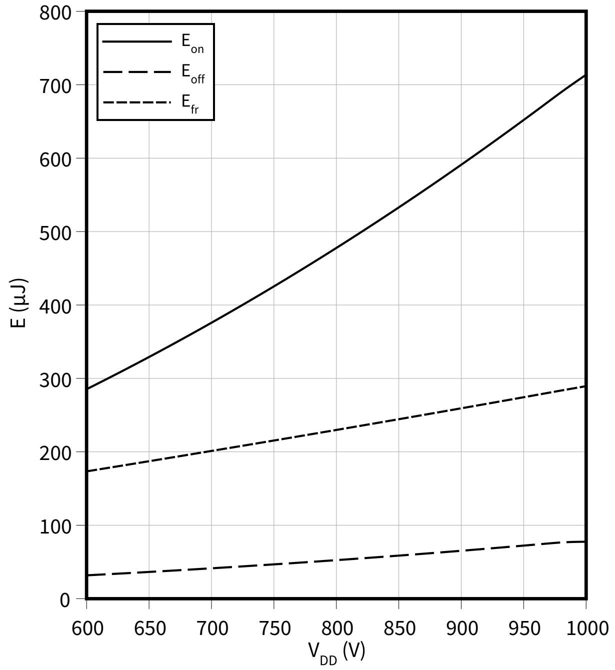
V_{GS} = 0/18 V, I_D = 27.3 A, T_{vj} = 175 °C, $R_{G,ext}$ = 2.3 Ω



Typical switching energy as a function of DC link voltage, test circuit in Fig. F, 2nd device own body diode: V_{GS} = -5 V

$E = f(V_{DD})$

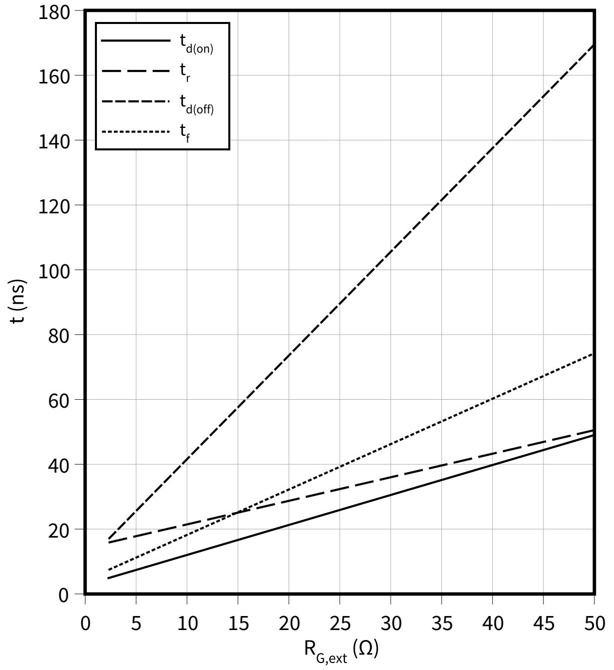
V_{GS} = -5/18 V, I_D = 27.3 A, T_{vj} = 175 °C, $R_{G,ext}$ = 2.3 Ω



Typical switching times as a function of gate resistance, test circuit in Fig. F, 2nd device own body diode: V_{GS} = 0 V

$t = f(R_{G,ext})$

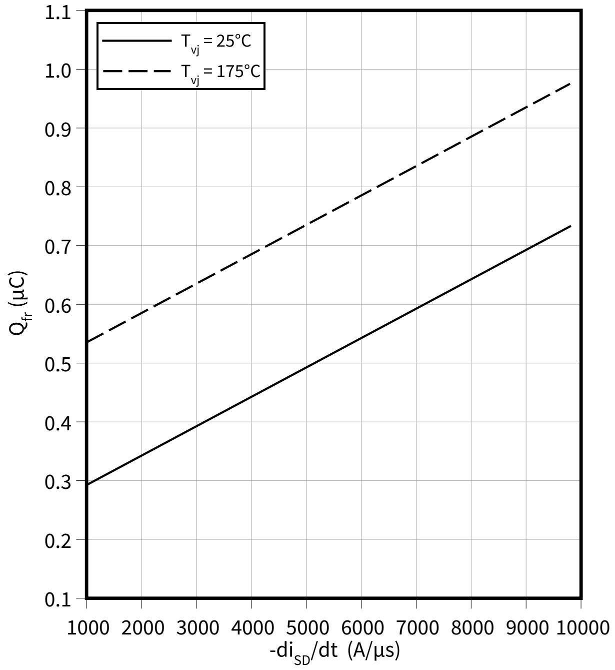
V_{GS} = 0/18 V, I_D = 27.3 A, T_{vj} = 175 °C, V_{DD} = 800 V



Typical reverse recovery charge as a function of reverse drain current slope, test circuit in Fig. F, 2nd device own body diode: V_{GS} = 0 V

$Q_{fr} = f(-di_{SD}/dt)$

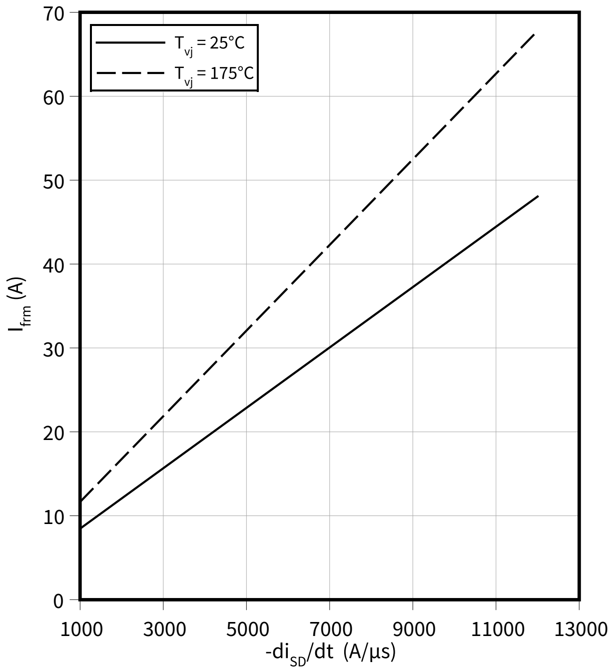
V_{GS} = 0/18 V, I_{SD} = 27.3 A, V_{DD} = 800 V



Typical reverse recovery current as a function of reverse drain current slope, test circuit in Fig. F, 2nd device own body diode: V_{GS} = 0 V

$I_{frm} = f(-di_{SD}/dt)$

V_{GS} = 0/18 V, I_{SD} = 27.3 A, V_{DD} = 800 V

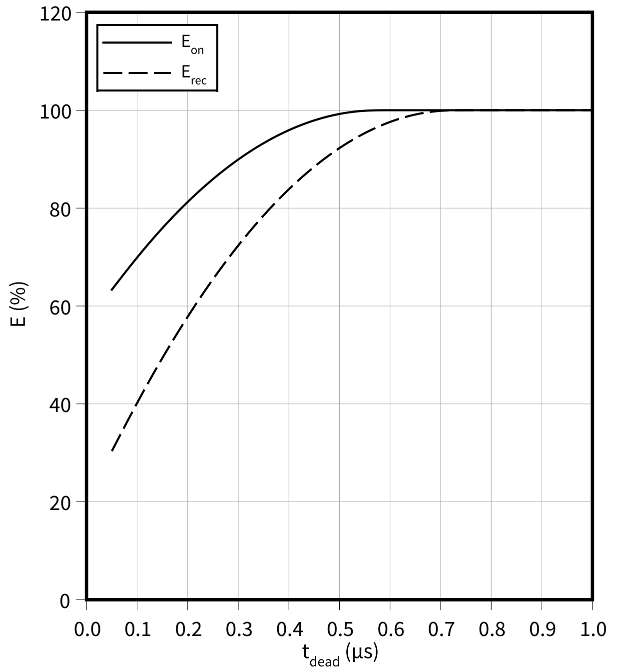


Typical switching energy as a function of dead time / blanking time, test circuit in Fig. F, 2nd device own body diode: V_{GS} = -5 V

$E = f(t_{dead})$

V_{GS} = 0/18 V, I_D = 27.3 A, T_{vj} = 175 °C, $R_{G,ext}$ = 2.3 Ω

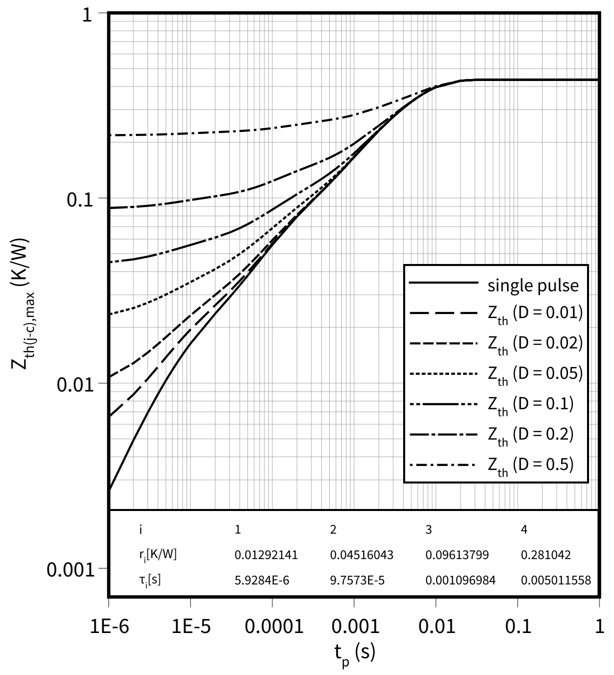
V_{DD} = 800 V



Max. transient thermal impedance (MOSFET/diode)

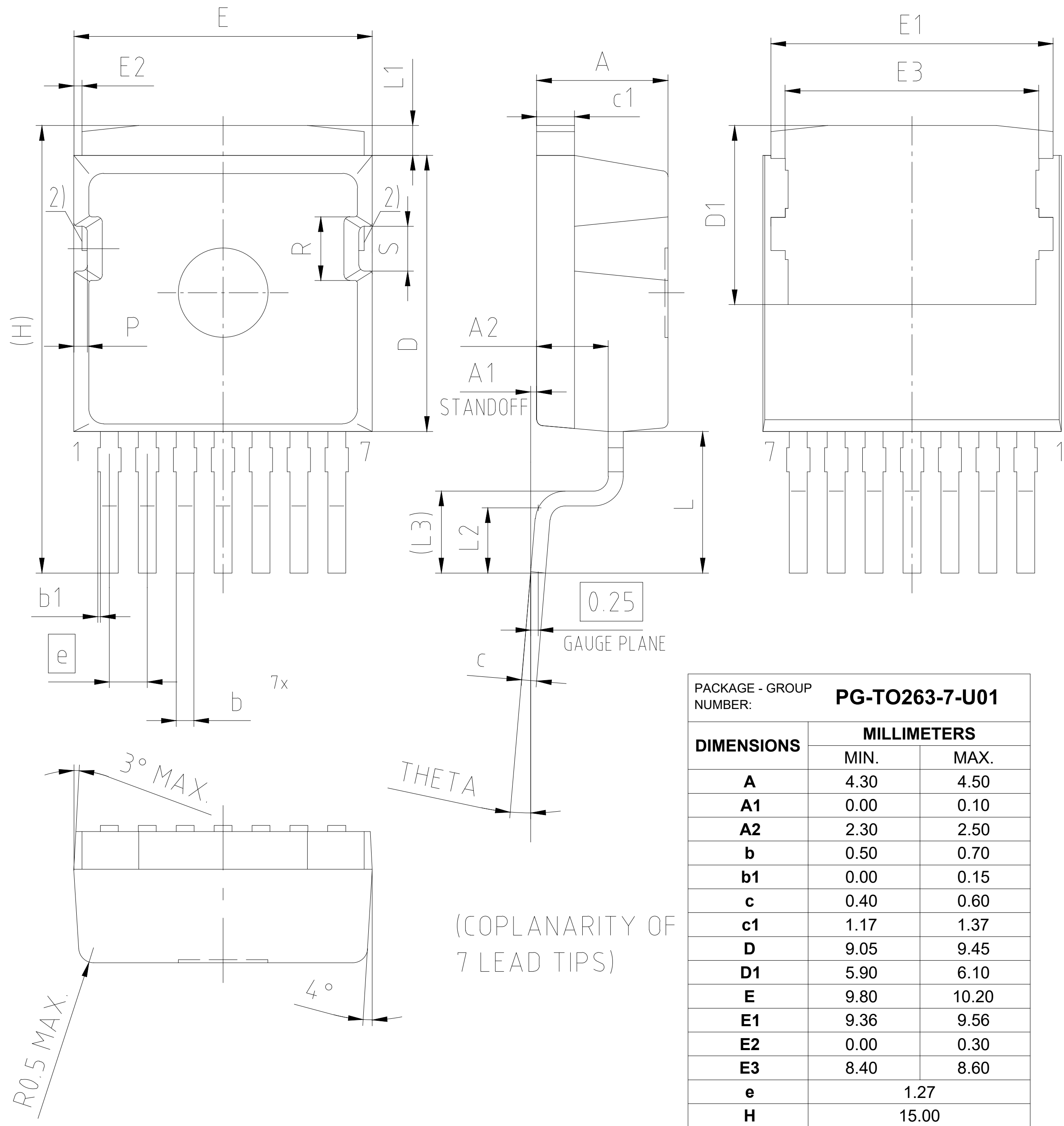
$Z_{th(j-c),max} = f(t_p)$

$D = t_p/T$



i	1	2	3	4
r_i[K/W]	0.01292141	0.04516043	0.09613799	0.281042
τ_i[s]	5.9284E-6	9.7573E-5	0.001096984	0.005011558

5 Package outlines



PACKAGE - GROUP NUMBER:	PG-TO263-7-U01	
DIMENSIONS	MILLIMETERS	
	MIN.	MAX.
A	4.30	4.50
A1	0.00	0.10
A2	2.30	2.50
b	0.50	0.70
b1	0.00	0.15
c	0.40	0.60
c1	1.17	1.37
D	9.05	9.45
D1	5.90	6.10
E	9.80	10.20
E1	9.36	9.56
E2	0.00	0.30
E3	8.40	8.60
e	1.27	
H	15.00	
L	4.20	5.20
L1	0.70	1.30
L2	1.70	2.30
L3	2.70	
P	0.35	0.55
R	2.03	2.23
S	1.40	1.60
THETA	0.00°	8.00°

NOTES:
1) ALL METAL SURFACES TIN PLATED EXCEPT AREA OF CUT
2) MOLD FILLING IS ACCEPTABLE AT THIS AREA

Figure 1

6 Testing conditions

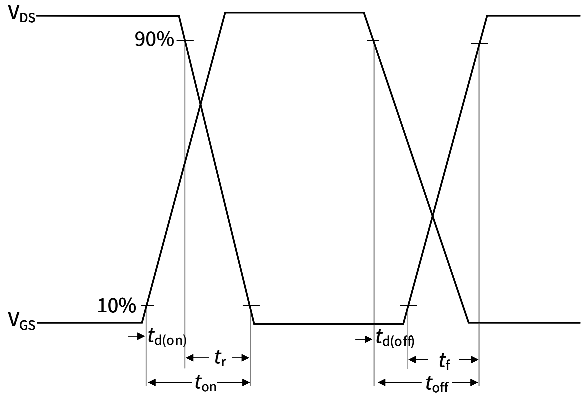


Figure A. **Definition of switching times**

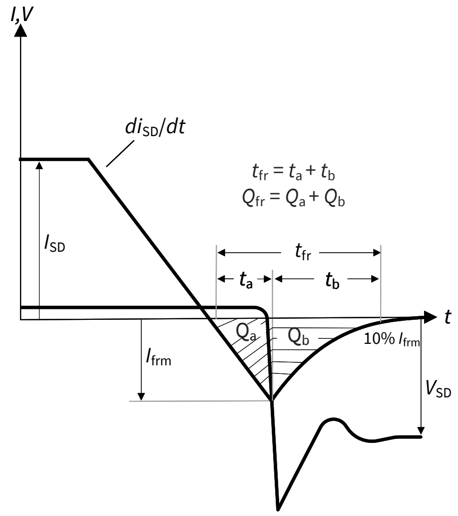


Figure B. **Definition of body diode switching characteristics**

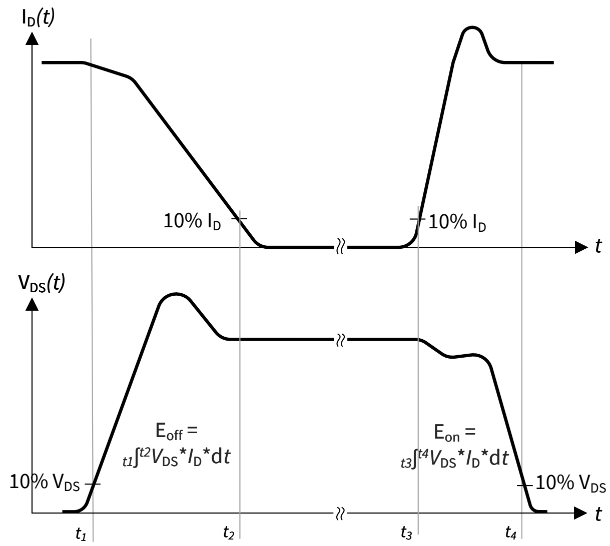


Figure C. **Definition of switching losses**

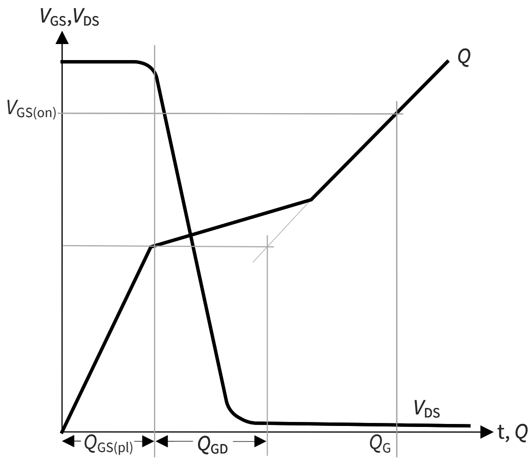


Figure D. **Definition of QGD**

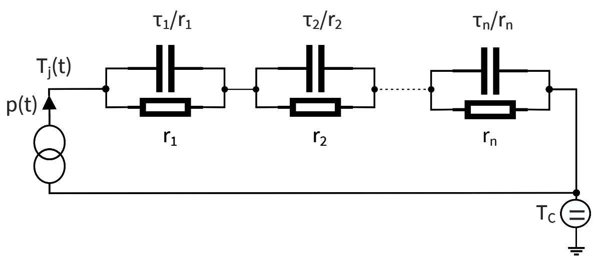


Figure E. **Thermal equivalent circuit**

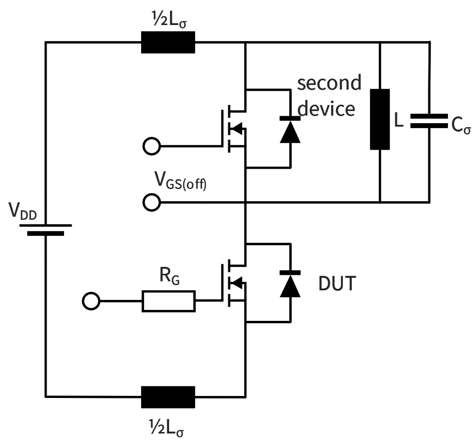


Figure F. **Dynamic test circuit**
Parasitic inductance L_σ,
Parasitic capacitor C_σ,

Figure 2

Revision history

Document revision	Date of release	Description of changes
0.10	2023-08-08	Preliminary datasheet
1.00	2023-09-29	Final datasheet
1.10	2024-01-12	Negative gate voltage values updated Resistance parameters updated Additional capacitance & charge values added $E = f(t_{dead})$ graph y-axis correction to percentage values Editorial changes
1.20	2024-07-02	Updated „Potential applications“ Corrected package name Corrected static and dynamic gate-source voltage Corrected unit of L to µH for "Avalanche energy, repetitive” Corrected value of E_{AR} in the Table 2 Corrected value of g_{fs} in the Table 4 Corrected diagrams "Typical transfer characteristic" and "Max. transient thermal impedance (MOSFET/diode)" Updated Figure D. Definition of QGD
1.30	2024-11-08	Corrected diagram $I_{frm} = f(-di_{SD}/dt)$ Editorial changes
1.40	2026-01-27	Increased I_{DM} in Table 2 Corrected conditions for Q_G, $Q_{GS(pl)}$ and Q_{GD} in Table 4 Added switching information for V_{GS} = -5/18 V in Table 4 and 6 and corresponding diagrams Added I_{SDC} in Table 5 Corrected test conditions and adapt values of the body diode in Table 6 Added SOA diagram on page 8 Added diagram $E = f(V_{DD})$ @ V_{GS} = 0/18 V Added diagram $E = f(V_{DD})$ @ V_{GS} = -5/18 V Editorial changes

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